



**THE DATASHEET OF  
PMD9010D,115**



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Kind regards,

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# PMD9010D

## MOSFET driver

Rev. 01 — 20 November 2006

Product data sheet

## 1. Product profile

### 1.1 General description

Two NPN transistors and high-speed switching diode connected in totem pole configuration in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package.

### 1.2 Features

- Two general-purpose transistors and one high-speed switching diode as driver
- Totem pole configuration
- Application-optimized pinout
- Internal connections to minimize layout effort
- Space-saving solution
- Reduces component count

### 1.3 Applications

- MOSFET driver

### 1.4 Quick reference data

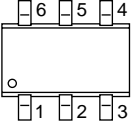
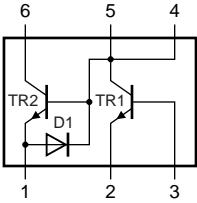
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor</b>						
$V_{CEO}$	collector-emitter voltage	open base	-	-	45	V
$I_C$	collector current		-	-	0.1	A
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	0.2	A
<b>Diode (D1)</b>						
$I_F$	forward current		-	-	-0.2	A
$V_F$	forward voltage	$I_F = -200$ mA	[1]	-	-1.1	V

[1] Pulse test:  $t_p \leq 300$   $\mu$ s;  $\delta \leq 0.02$ .

## 2. Pinning information

**Table 2. Pinning**

Pin	Symbol	Description	Simplified outline	Symbol
1	OUT	output		
2	GND	ground		
3	IN	input		
4	RC	collector resistor		
5	RC	collector resistor		
6	VCC	supply voltage		

006aaa657

## 3. Ordering information

**Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
PMD9010D	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457

## 4. Marking

**Table 4. Marking codes**

Type number	Marking code
PMD9010D	AA

## 5. Limiting values

**Table 5. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Min	Max	Unit
<b>Transistor 1 (TR1)</b>					
$V_{CBO}$	collector-base voltage	open emitter	-	50	V
$V_{CEO}$	collector-emitter voltage	open base	-	45	V
$V_{EBO}$	emitter-base voltage	open collector	-	5	V
$I_C$	collector current		-	0.1	A
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1$ ms	-	0.2	A

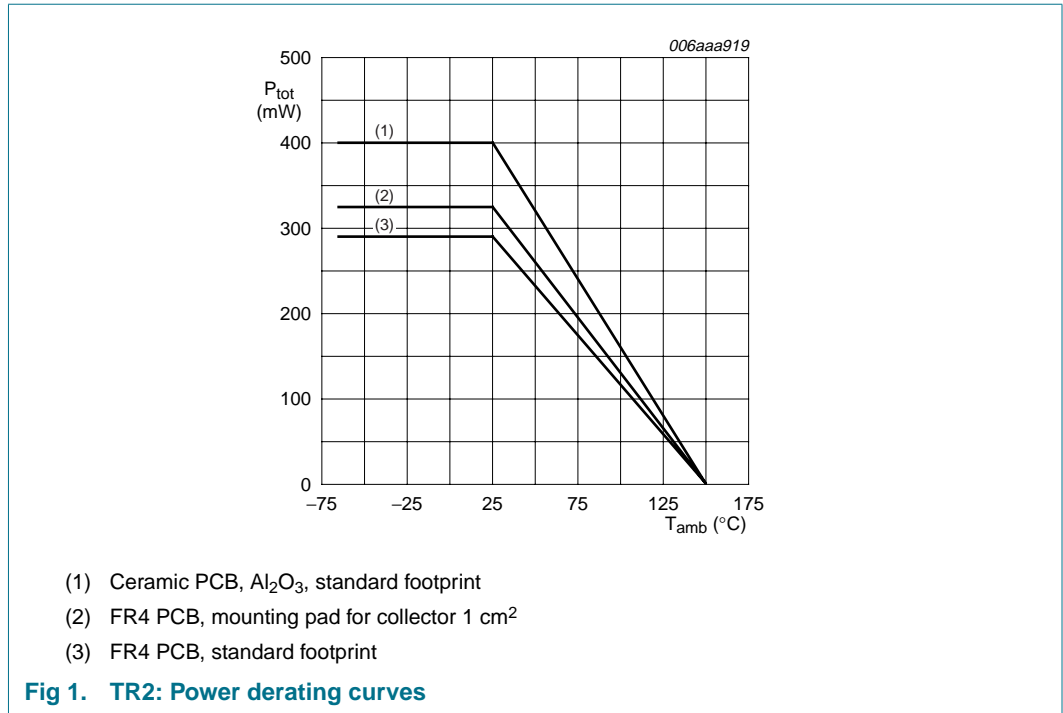
**Table 5. Limiting values ...continued***In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Min	Max	Unit	
<b>Transistor 2 (TR2)</b>						
$V_{CBO}$	collector-base voltage	open emitter	-	50	V	
$V_{CEO}$	collector-emitter voltage	open base	-	45	V	
$I_C$	collector current		-	0.1	A	
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1$ ms	-	0.2	A	
$I_{BM}$	peak base current	single pulse; $t_p \leq 1$ ms	-	0.2	A	
$P_{tot}$	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	290	mW
			[2]	-	325	mW
			[3]	-	400	mW
<b>Diode (D1)</b>						
$I_F$	forward current		-	-0.2	A	
$I_{FRM}$	repetitive peak forward current	$t_p \leq 1$ ms; $\delta \leq 0.25$	-	-0.6	A	
$I_{FSM}$	non-repetitive peak forward current	square wave				
		$t_p = 1$ $\mu$ s	-	-9	A	
		$t_p = 100$ $\mu$ s	-	-3	A	
		$t_p = 10$ ms	-	-1.7	A	
<b>Device</b>						
$T_j$	junction temperature		-	150	°C	
$T_{amb}$	ambient temperature		-65	+150	°C	
$T_{stg}$	storage temperature		-65	+150	°C	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

[3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



## 6. Thermal characteristics

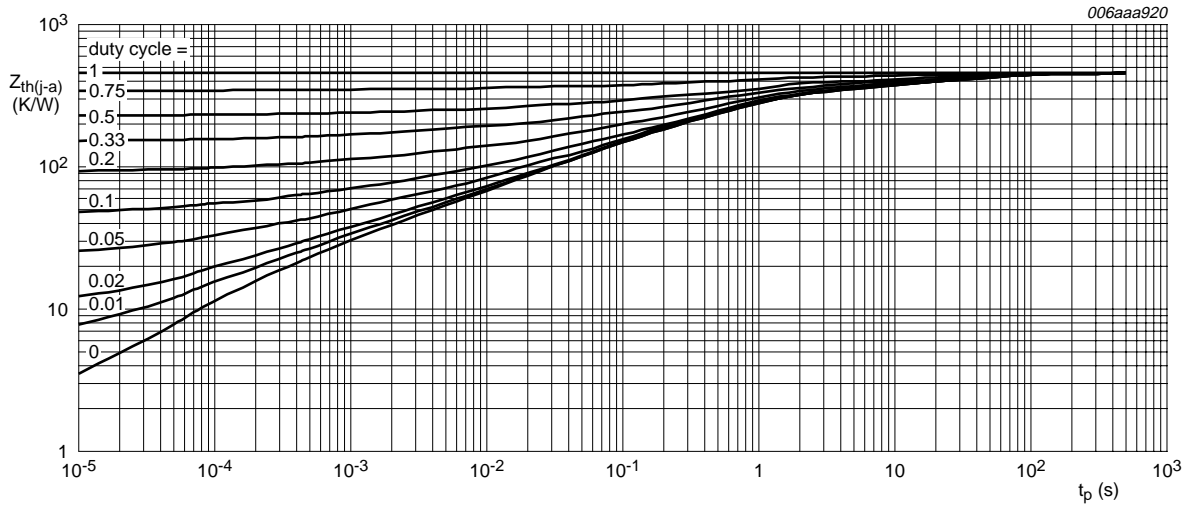
**Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
<b>Transistor 2 (TR2)</b>							
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	430	K/W
			[2]	-	-	385	K/W
			[3]	-	-	312	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

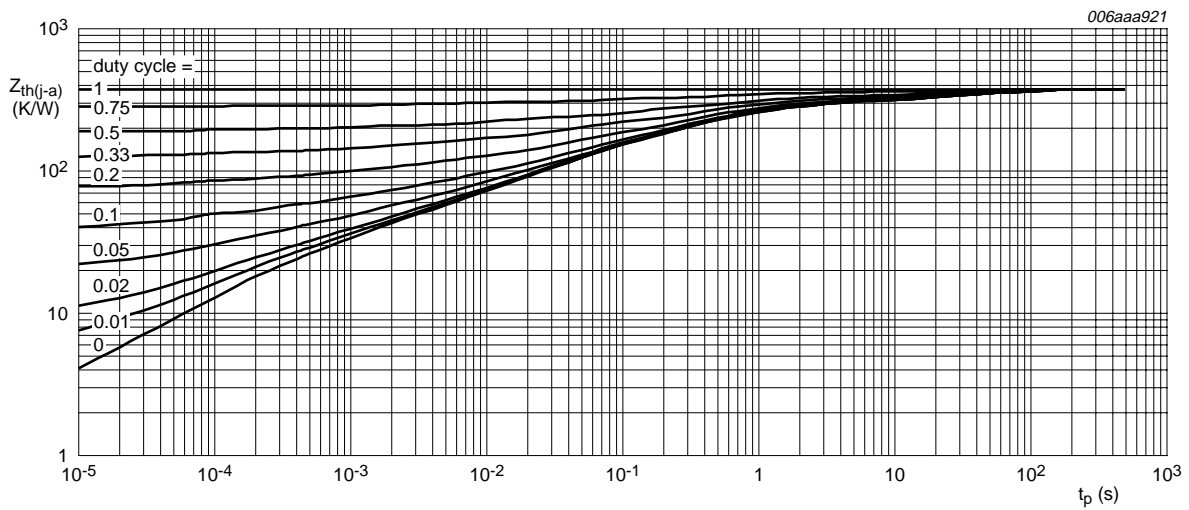
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

[3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



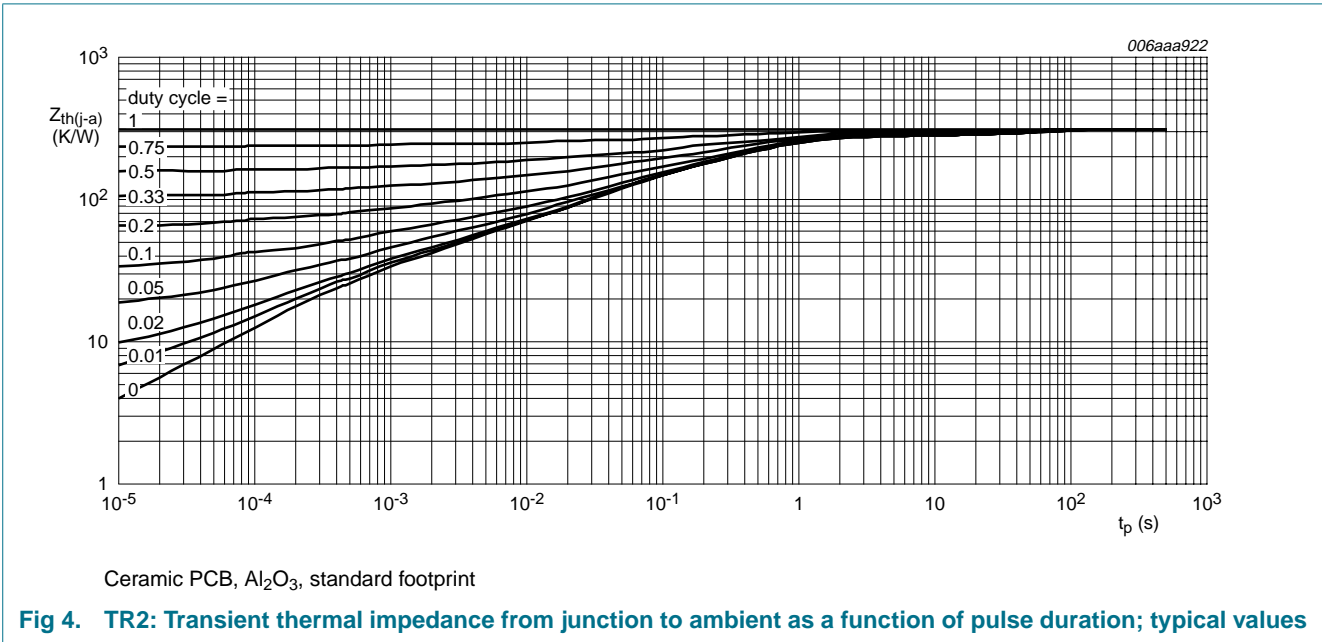
FR4 PCB, standard footprint

Fig 2. TR2: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>

Fig 3. TR2: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



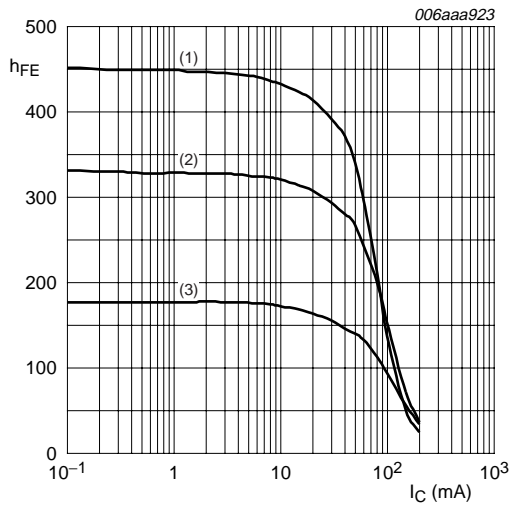
## 7. Characteristics

**Table 7. Characteristics**

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

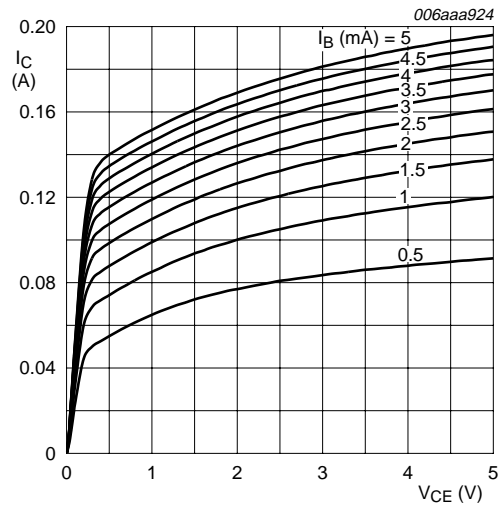
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Transistor 1 (TR1)</b>						
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 30\text{ V}; I_E = 0\text{ A}$	-	-	100	nA
$I_{CEO}$	collector-emitter cut-off current	$V_{CE} = 30\text{ V}; I_B = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	50	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	0.1	mA
$h_{FE}$	DC current gain	$V_{CE} = 5\text{ V}; I_C = 1\text{ mA}$	200	290	450	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	-	60	200	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	-	0.7	-	V
$V_{BE}$	base-emitter voltage	$V_{CE} = 5\text{ V}; I_C = 2\text{ mA}$	-	660	-	mV
<b>Transistor 2 (TR2)</b>						
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 30\text{ V}; I_E = 0\text{ A}$	-	-	15	nA
		$V_{CB} = 30\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	5	$\mu\text{A}$
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	-	60	200	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	-	200	400	mV
		$I_C = 200\text{ mA}; I_B = 20\text{ mA}$	-	340	500	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	-	0.7	-	V
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	-	0.9	-	V
$V_{BE}$	base-emitter voltage	$V_{CE} = 5\text{ V}; I_C = 2\text{ mA}$	610	660	710	mV
		$V_{CE} = 5\text{ V}; I_C = 10\text{ mA}$	-	-	770	mV
<b>Diode (D1)</b>						
$V_F$	forward voltage	$I_F = -200\text{ mA}$	[1]	-	-1.1	V
<b>TR2 and D1</b>						
$h_{FE}$	DC current gain	$V_{CE} = 5\text{ V}; I_C = 1\text{ mA}$	200	290	450	
		$V_{CE} = 5\text{ V}; I_C = 100\text{ mA}$	95	140	-	
		$V_{CE} = 5\text{ V}; I_C = 200\text{ mA}$	24	35	-	
<b>Device</b>						
$t_d$	delay time	$I_C = 0.05\text{ A}; I_B = 2.5\text{ mA}$	-	13	-	ns
$t_r$	rise time		-	77	-	ns
$t_{on}$	turn-on time		-	90	-	ns
$t_s$	storage time		-	853	-	ns
$t_f$	fall time		-	205	-	ns
$t_{off}$	turn-off time		-	1058	-	ns

[1] Pulse test:  $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$ .



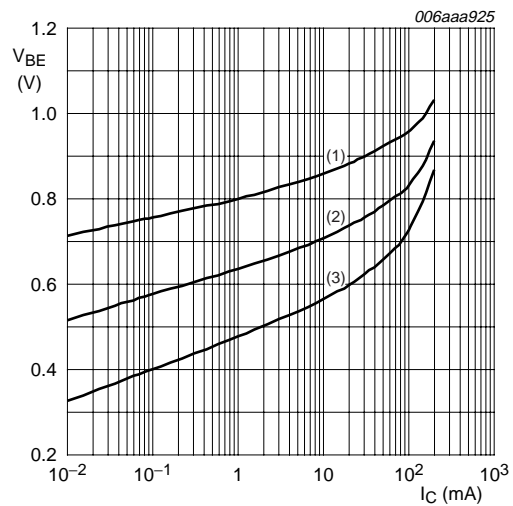
$V_{CE} = 5\text{ V}$   
 (1)  $T_{amb} = 100\text{ }^{\circ}\text{C}$   
 (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$   
 (3)  $T_{amb} = -55\text{ }^{\circ}\text{C}$

**Fig 5. TR1: DC current gain as a function of collector current; typical values**



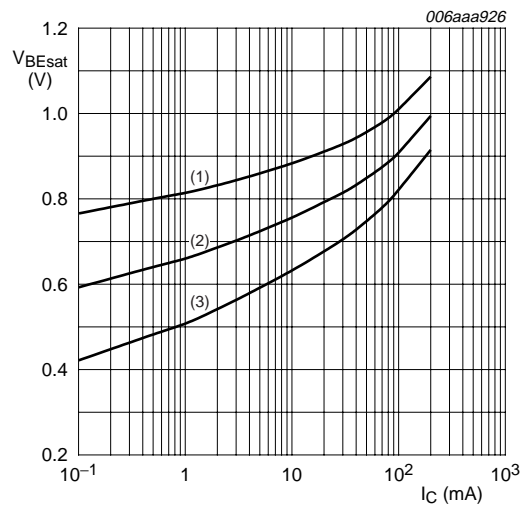
$T_{amb} = 25\text{ }^{\circ}\text{C}$

**Fig 6. TR1: Collector current as a function of collector-emitter voltage; typical values**



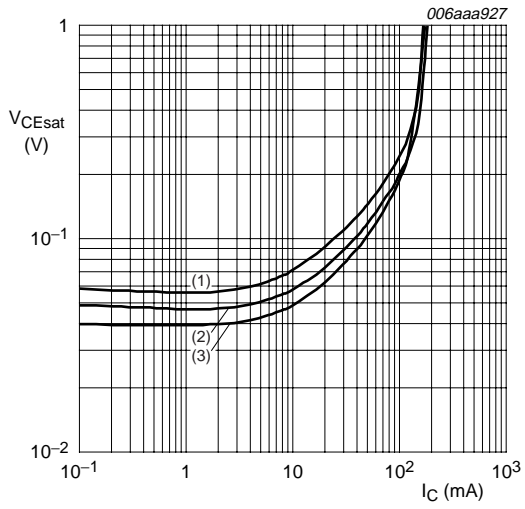
$V_{CE} = 5\text{ V}$   
 (1)  $T_{amb} = -55\text{ }^{\circ}\text{C}$   
 (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$   
 (3)  $T_{amb} = 100\text{ }^{\circ}\text{C}$

**Fig 7. TR1: Base-emitter voltage as a function of collector current; typical values**



$I_C/I_B = 20$   
 (1)  $T_{amb} = -55\text{ }^{\circ}\text{C}$   
 (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$   
 (3)  $T_{amb} = 100\text{ }^{\circ}\text{C}$

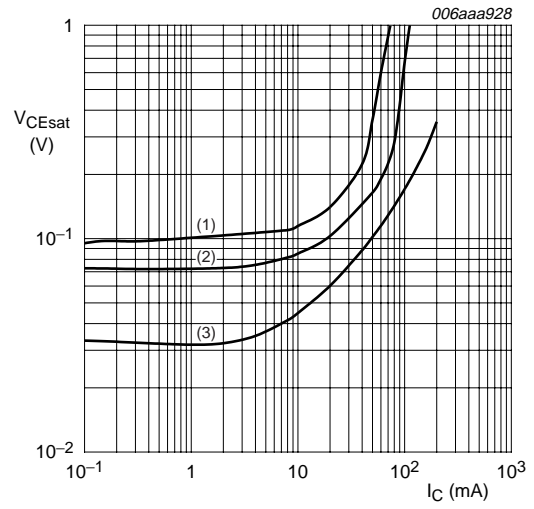
**Fig 8. TR1: Base-emitter saturation voltage as a function of collector current; typical values**



$I_C/I_B = 20$

- (1)  $T_{amb} = 100\text{ °C}$
- (2)  $T_{amb} = 25\text{ °C}$
- (3)  $T_{amb} = -55\text{ °C}$

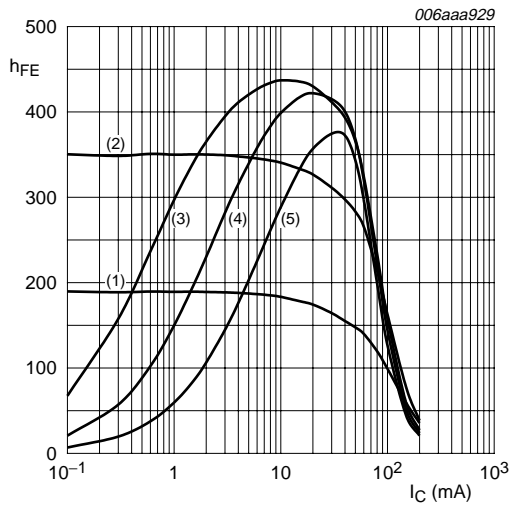
**Fig 9. TR1: Collector-emitter saturation voltage as a function of collector current; typical values**



$T_{amb} = 25\text{ °C}$

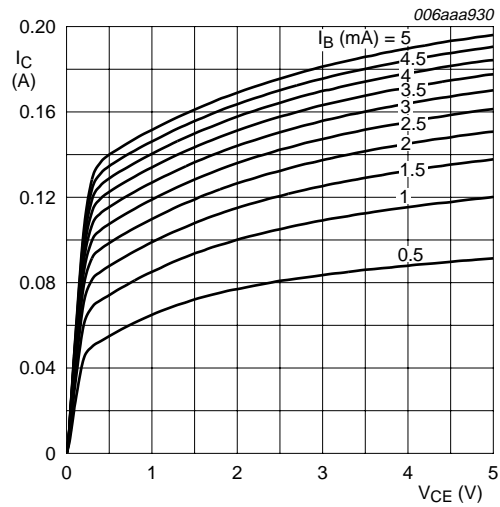
- (1)  $I_C/I_B = 100$
- (2)  $I_C/I_B = 50$
- (3)  $I_C/I_B = 10$

**Fig 10. TR1: Collector-emitter saturation voltage as a function of collector current; typical values**



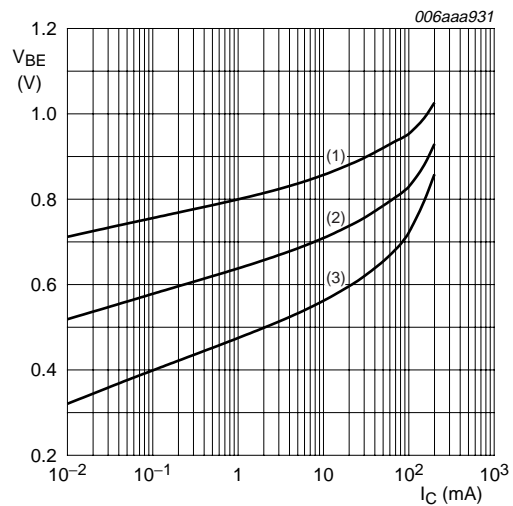
$V_{CE} = 5\text{ V}$   
 (1)  $T_{amb} = -55\text{ }^{\circ}\text{C}$   
 (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$   
 (3)  $T_{amb} = 100\text{ }^{\circ}\text{C}$   
 (4)  $T_{amb} = 125\text{ }^{\circ}\text{C}$   
 (5)  $T_{amb} = 150\text{ }^{\circ}\text{C}$

**Fig 11. TR2 and D1: DC current gain as a function of collector current; typical values**



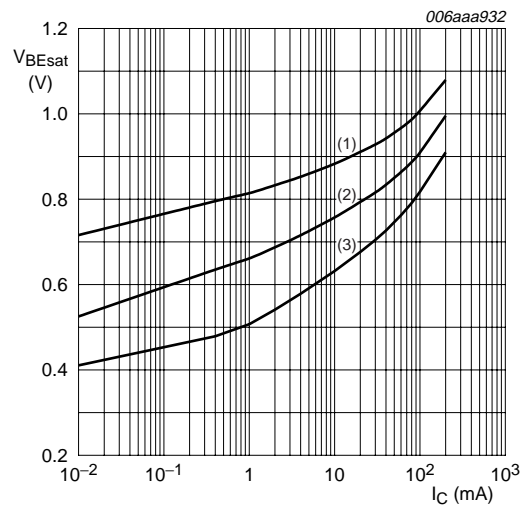
$T_{amb} = 25\text{ }^{\circ}\text{C}$

**Fig 12. TR2: Collector current as a function of collector-emitter voltage; typical values**



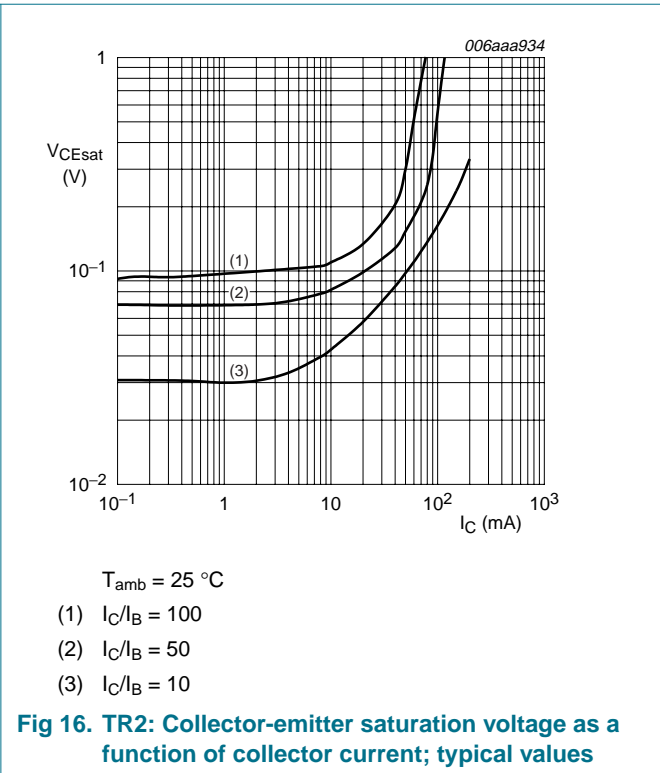
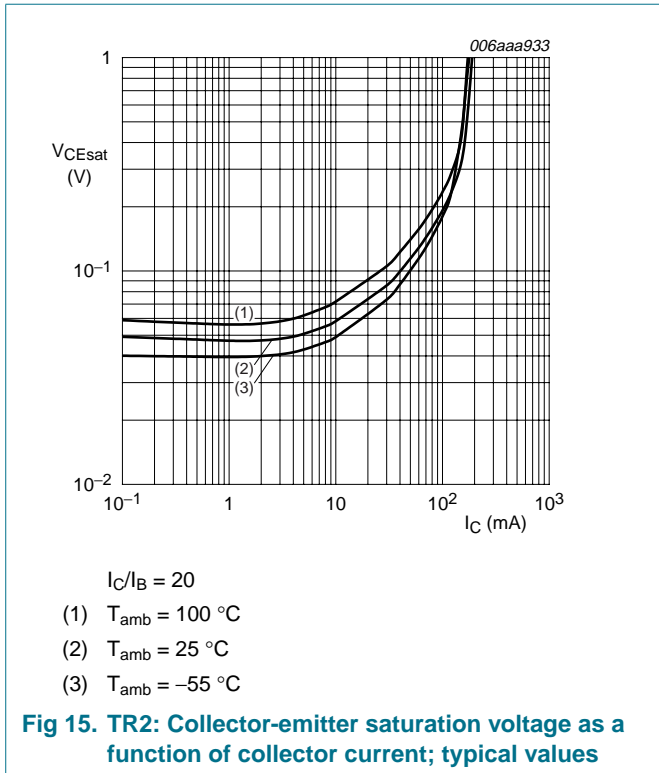
$V_{CE} = 5\text{ V}$   
 (1)  $T_{amb} = -55\text{ }^{\circ}\text{C}$   
 (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$   
 (3)  $T_{amb} = 100\text{ }^{\circ}\text{C}$

**Fig 13. TR2: Base-emitter voltage as a function of collector current; typical values**

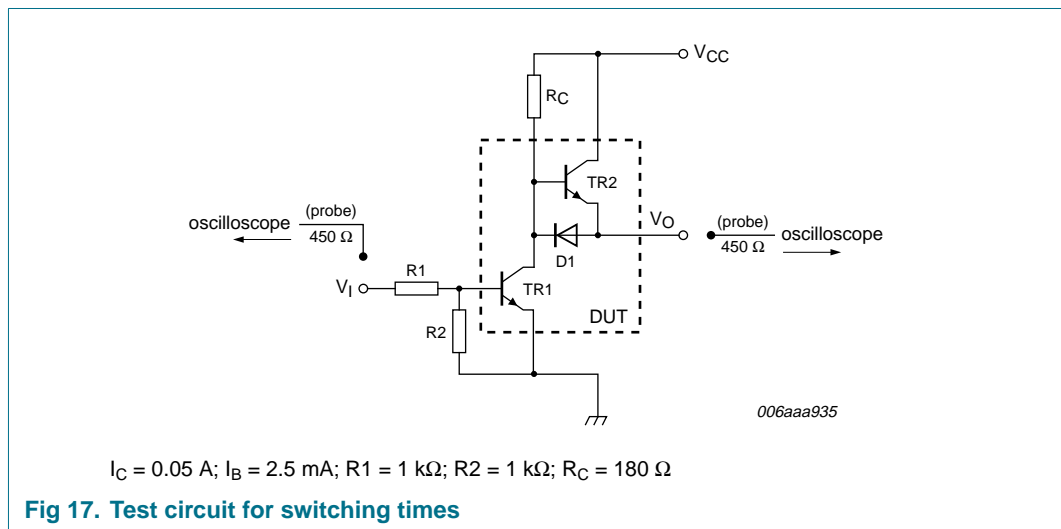


$I_C/I_B = 20$   
 (1)  $T_{amb} = -55\text{ }^{\circ}\text{C}$   
 (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$   
 (3)  $T_{amb} = 100\text{ }^{\circ}\text{C}$

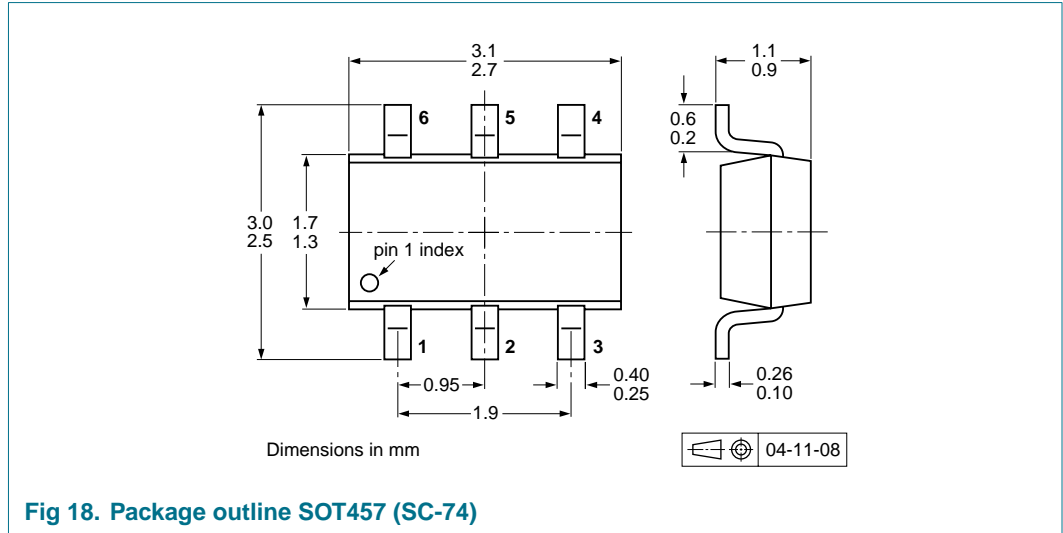
**Fig 14. TR2: Base-emitter saturation voltage as a function of collector current; typical values**



## 8. Test information



## 9. Package outline



## 10. Packing information

**Table 8. Packing methods**

The indicated -xxx are the last three digits of the 12NC ordering code.<sup>[1]</sup>

Type number	Package	Description	Packing quantity	
			3000	10000
PMD9010D	SOT457	4 mm pitch, 8 mm tape and reel; T1 <sup>[2]</sup>	-115	-135
		4 mm pitch, 8 mm tape and reel; T2 <sup>[3]</sup>	-125	-165

[1] For further information and the availability of packing methods, see [Section 14](#).

[2] T1: normal taping

[3] T2: reverse taping

### 11. Soldering

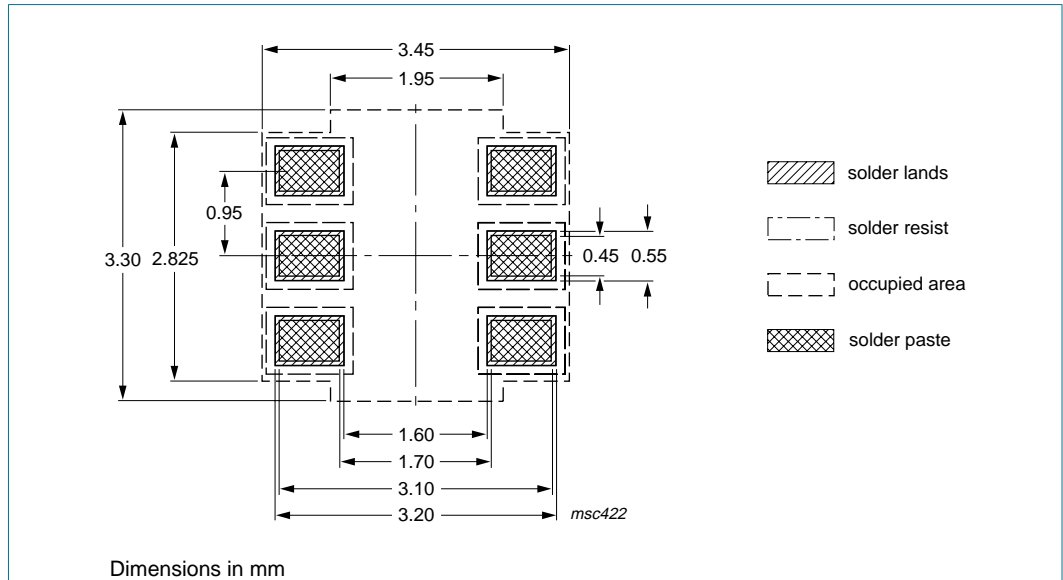


Fig 19. Reflow soldering footprint SOT457 (SC-74)

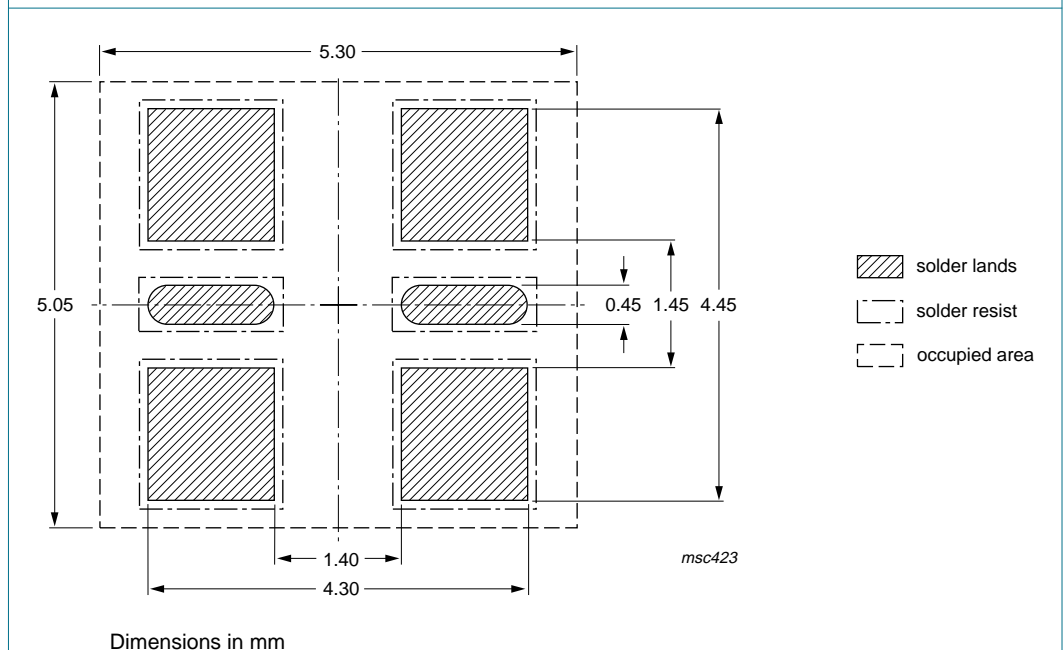


Fig 20. Wave soldering footprint SOT457 (SC-74)

## 12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMD9010D_1	20061120	Product data sheet	-	-

## 13. Legal information

### 13.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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Date of release: 20 November 2006

Document identifier: PMD9010D\_1

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